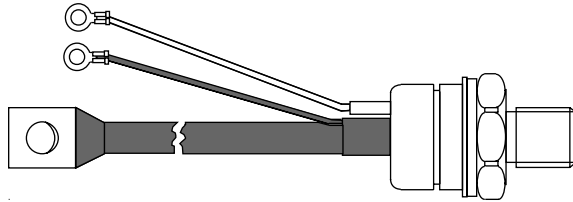


## Phase Control Thyristors (Stud Version), 230 A



TO-209AB (TO-93)

**FEATURES**

- Center amplifying gate
- International standard case TO-209AB (TO-93)
- Hermetic metal case with ceramic insulator (Also available with glass-metal seal up to 1200 V)
- Compression bonded encapsulation for heavy duty operations such as severe thermal cycling
- Lead (Pb)-free
- Designed and qualified for industrial level


**RoHS**  
COMPLIANT

**PRODUCT SUMMARY**

$I_{T(AV)}$	230 A
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**TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

**MAJOR RATINGS AND CHARACTERISTICS**

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		230	A
	$T_C$	85	°C
$I_{T(RMS)}$		360	A
$I_{TSM}$	50 Hz	5700	A
	60 Hz	5970	
$I^2t$	50 Hz	163	kA <sup>2</sup> s
	60 Hz	149	
$V_{DRM}/V_{RRM}$		400 to 1600	V
$t_q$	Typical	100	μs
$T_J$		- 40 to 125	°C

**ELECTRICAL SPECIFICATIONS**
**VOLTAGE RATINGS**

TYPE NUMBER	VOLTAGE CODE	$V_{DRM}/V_{RRM}$ , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	$V_{RSM}$ , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM mA
ST230S	04	400	500	30
	08	800	900	
	12	1200	1300	
	16	1600	1700	

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average on-state current at case temperature	$I_{T(AV)}$	180° conduction, half sine wave		230	A	
				85	°C	
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 78 °C case temperature		360		
Maximum peak, one-cycle non-repetitive surge current	$I_{TSM}$	t = 10 ms	No voltage reapplied	5700	A	
		t = 8.3 ms				5970
		t = 10 ms	100 % $V_{RRM}$ reapplied	4800		
		t = 8.3 ms				5000
Maximum $I^2t$ for fusing	$I^2t$	t = 10 ms	No voltage reapplied	163	kA <sup>2</sup> s	
		t = 8.3 ms				148
		t = 10 ms	100 % $V_{RRM}$ reapplied	115		
		t = 8.3 ms				105
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied		1630	kA <sup>2</sup> /s	
Low level value of threshold voltage	$V_{T(TO)1}$	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum		0.92	V	
High level value of threshold voltage	$V_{T(TO)2}$	$(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum		0.98		
Low level value of on-state slope resistance	$r_{t1}$	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum		0.88	mΩ	
High level value of on-state slope resistance	$r_{t2}$	$(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum		0.81		
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 720$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sine pulse		1.55	V	
Maximum holding current	$I_H$	$T_J = 25$ °C, anode supply 12 V resistive load		600	mA	
Maximum (typical) latching current	$I_L$			1000 (300)		

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	$di/dt$	Gate drive 20 V, 20 Ω, $t_r \leq 1$ μs $T_J = T_J$ maximum, anode voltage $\leq 80\%$ $V_{DRM}$		1000	A/μs
Typical delay time	$t_d$	Gate current 1 A, $di_g/dt = 1$ A/μs $V_d = 0.67\%$ $V_{DRM}$ , $T_J = 25$ °C		1.0	μs
Typical turn-off time	$t_q$	$I_{TM} = 300$ A, $T_J = T_J$ maximum, $di/dt = 20$ A/μs, $V_R = 50$ V, $dV/dt = 20$ V/μs, gate 0 V 100 Ω, $t_p = 500$ μs		100	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum critical rate of rise of off-state voltage	$dV/dt$	$T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$		500	V/μs
Maximum peak reverse and off-state leakage current	$I_{RRM}$ , $I_{DRM}$	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied		30	mA



<b>TRIGGERING</b>						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
				TYP.	MAX.	
Maximum peak gate power	$P_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms		10.0		W
Maximum average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum, $f = 50$ Hz, $d\% = 50$		2.0		
Maximum peak positive gate current	$I_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms		3.0		A
Maximum peak positive gate voltage	$+V_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms		20		V
Maximum peak negative gate voltage	$-V_{GM}$			5.0		
DC gate current required to trigger	$I_{GT}$	$T_J = -40$ °C	Maximum required gate trigger/current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	180	-	mA
		$T_J = 25$ °C		90	150	
		$T_J = 125$ °C		40	-	
DC gate voltage required to trigger	$V_{GT}$	$T_J = -40$ °C		2.9	-	V
		$T_J = 25$ °C		1.8	3.0	
		$T_J = 125$ °C		1.2	-	
DC gate current not to trigger	$I_{GD}$	$T_J = T_J$ maximum	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated $V_{DRM}$ anode to cathode applied	10		mA
DC gate voltage not to trigger	$V_{GD}$			0.25		V

<b>THERMAL AND MECHANICAL SPECIFICATIONS</b>				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction temperature range	$T_J$		- 40 to 125	°C
Maximum storage temperature range	$T_{Stg}$		- 40 to 150	
Maximum thermal resistance, junction to case	$R_{thJC}$	DC operation	0.10	K/W
Maximum thermal resistance, case to heatsink	$R_{thC-hs}$	Mounting surface, smooth, flat and greased	0.04	
Mounting torque, $\pm 10$ %		Non-lubricated threads	31 (275)	N · m (lbf · in)
		Lubricated threads	24.5 (210)	
Approximate weight			280	g
Case style		See dimensions - link at the end of datasheet	TO-209AB (TO-93)	

<b><math>\Delta R_{thJC}</math> CONDUCTION</b>				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.016	0.012	$T_J = T_J$ maximum	K/W
120°	0.019	0.020		
90°	0.025	0.027		
60°	0.036	0.037		
30°	0.060	0.060		

**Note**

- The table above shows the increment of thermal resistance  $R_{thJC}$  when devices operate at different conduction angles than DC

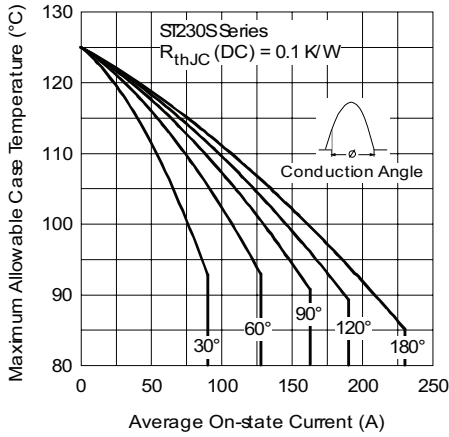


Fig. 1 - Current Ratings Characteristics

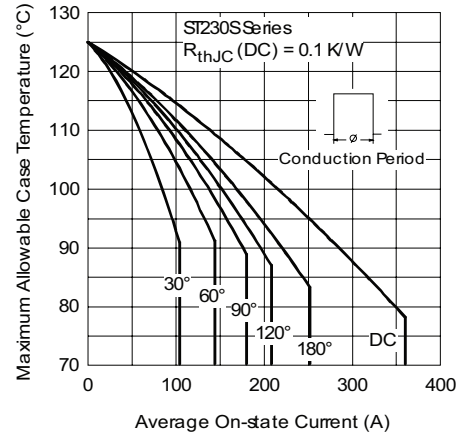


Fig. 2 - Current Ratings Characteristics

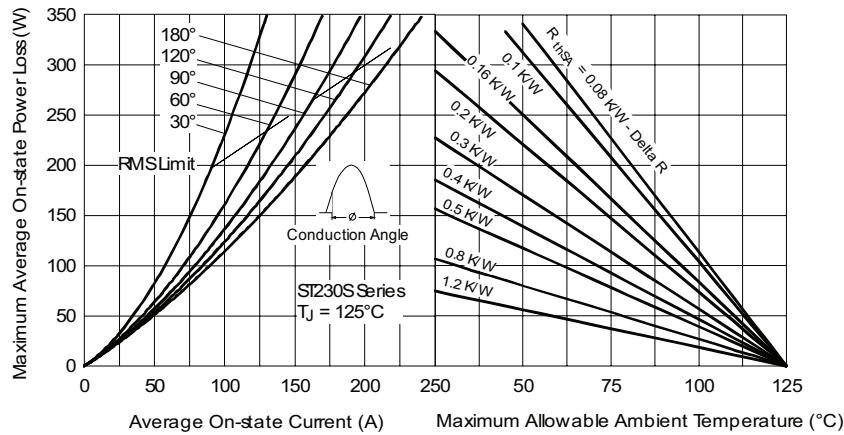


Fig. 3 - On-State Power Loss Characteristics

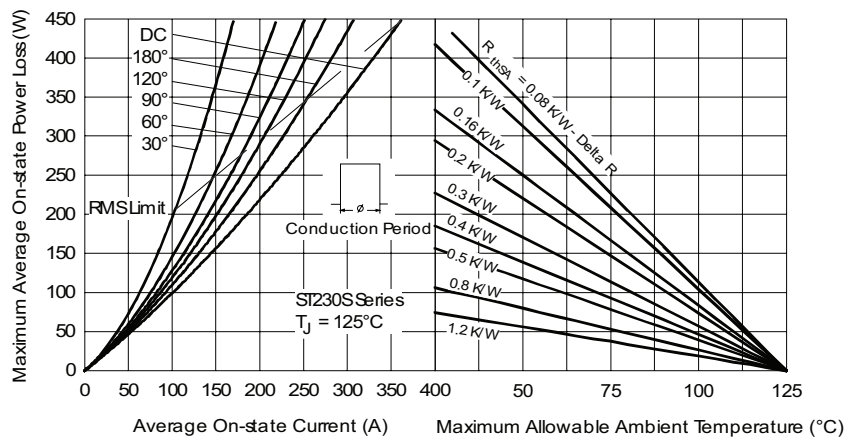


Fig. 4 - On-State Power Loss Characteristics

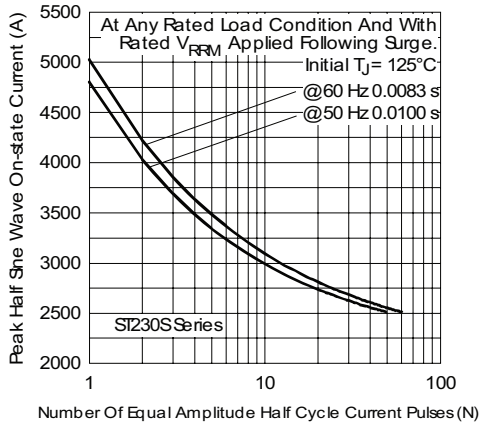


Fig. 5 - Maximum Non-Repetitive Surge Current

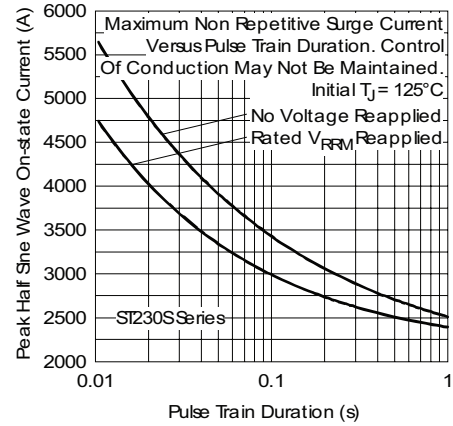


Fig. 6 - Maximum Non-Repetitive Surge Current

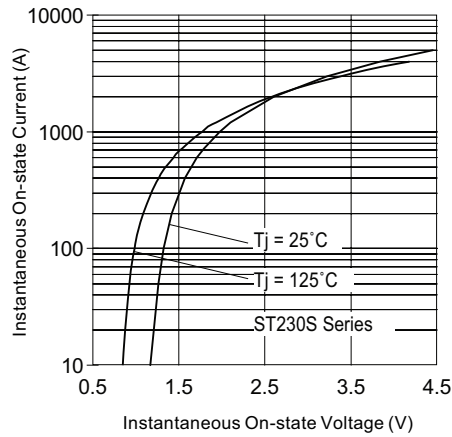


Fig. 7 - On-State Voltage Drop Characteristics

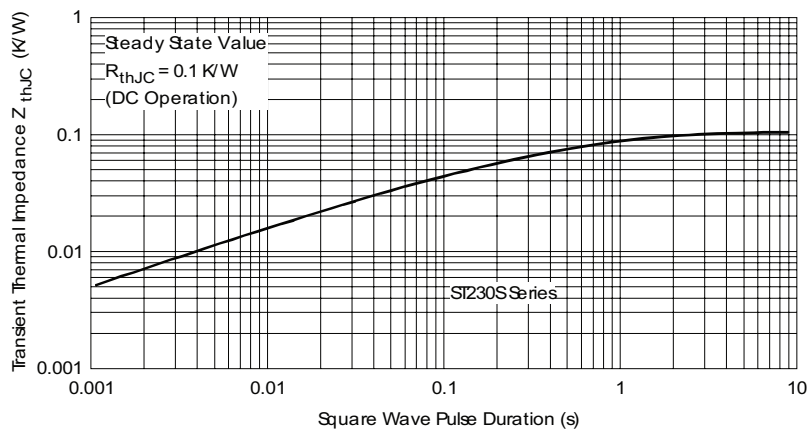


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

# ST230SPbF Series

Vishay High Power Products

Phase Control Thyristors  
(Stud Version), 230 A

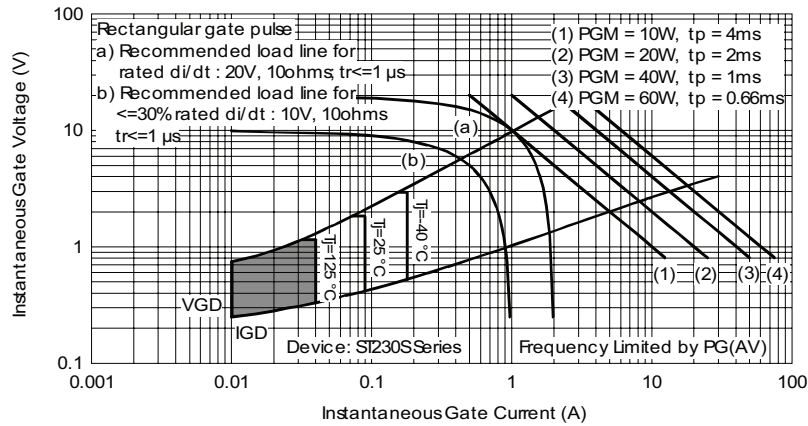


Fig. 9 - Gate Characteristics

## ORDERING INFORMATION TABLE

Device code	<b>ST</b>	<b>23</b>	<b>0</b>	<b>S</b>	<b>16</b>	<b>P</b>	<b>0</b>	<b>V</b>	<b>PbF</b>
	(1)	(2)	(3)	(4)	(5)	(6)	(7)	(8)	(9)

- 1** - Thyristor
- 2** - Essential part number
- 3** - 0 = Converter grade
- 4** - S = Compression bonding stud
- 5** - Voltage code x 100 =  $V_{RRM}$  (see Voltage Ratings table)
- 6** - P = Stud base 3/4"-16UNF2A threads
- 7** - 0 = Eyelet terminals (gate and auxiliary cathode leads)  
1 = Fast-on terminals (gate and auxiliary cathode leads)
- 8** - • V = Glass-metal seal (only up to 1200 V)  
• None = Ceramic housing (over 1200 V)
- 9** - Lead (Pb)-free

Note: For metric device M16 x 1.5 contact factory

LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95077">http://www.vishay.com/doc?95077</a>



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## TO-209AB (TO-93)

**DIMENSIONS** in millimeters (inches)

Case Style TO-209AB (TO-93)

